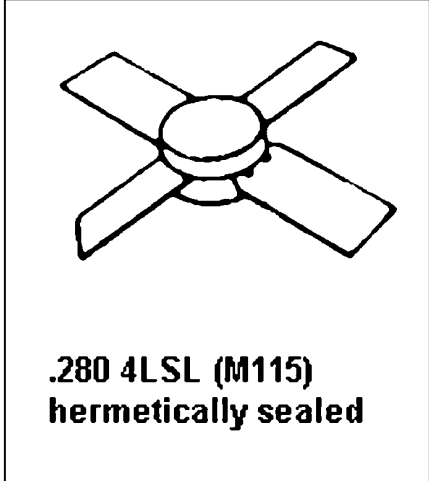


SD1526-01

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

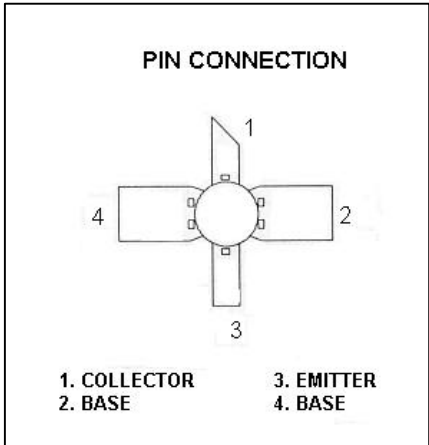
Features

- GOLD METALLIZATION
 - 960 - 1215 MHz
 - P_{OUT} = 5.0 WATTS
 - G_P = 9.5 dB MINIMUM
 - EMITTER BALLASTED
 - INFINITE VSWR CAPABILITY @ RATED CONDITIONS
 - INPUT MATCHED, COMMON BASE CONFIGURATION
-



DESCRIPTION:

The SD1526-01 is a gold metallized, silicon NPN power transistor designed for pulsed applications with low duty cycles such as IFF, DME, and TACAN. Internal impedance matching is utilized for broadband performance and simplified external matching.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

| Symbol | Parameter | Value | Unit |
|-------------------|---------------------------|-------------|------|
| V _{CBO} | Collector-Base Voltage | 45 | V |
| V _{CES} | Collector-Emitter Voltage | 45 | V |
| V _{EBO} | Emitter-Base Voltage | 3.5 | V |
| I _C | Device Current | 1 | A |
| P _{DISS} | Power Dissipation | 21.9 | W |
| T _{STG} | Storage Temperature | -65 to +150 | °C |
| T _J | Junction Temperature | 200 | °C |

Thermal Data

| | | | |
|----------------------|----------------------------------|-----|------|
| R _{TH(J-C)} | Thermal Resistance Junction-case | 8.0 | °C/W |
|----------------------|----------------------------------|-----|------|

ELECTRICAL SPECIFICATIONS (T_{case} = 25 °C)
STATIC

| Symbol | Test Conditions | | Value | | | Unit |
|-------------------------|------------------------------|---------------------------|-------|------|------|------|
| | | | Min. | Typ. | Max. | |
| BV_{CBO} | I_C = 10 mA | I_B = 0 | 45 | --- | --- | V |
| BV_{CES} | I_C = 25 mA | V_{BE} = 0 | 45 | --- | --- | V |
| BV_{EBO} | I_E = 10 mA | I_C = 0 | 3.5 | --- | --- | V |
| I_{CES} | V_{CE} = 28 V | V_{BE} = 0 | --- | --- | 1.0 | mA |

DYNAMIC

| Symbol | Test Conditions | | Value | | | Unit |
|----------------------------|--------------------------|------------------------------|-------|------|------|------|
| | | | Min. | Typ. | Max. | |
| P_{OUT} ** | f = 1090 MHz | V_{CC} = 28 V | --- | 6.0 | --- | W |
| G_P | f = 1090 MHz | V_{CC} = 28 V | --- | 9.5 | --- | dB |
| P_{OUT} ** | f = 1025–1150 MHz | V_{CC} = 28 V | 5.0 | --- | --- | W |
| G_P | f = 1025–1150 MHz | V_{CC} = 28 V | 9.5 | --- | --- | dB |
| P_{OUT} *** | f = 960–1215 MHz | V_{CC} = 28 V | --- | 4.0 | --- | W |
| G_P | f = 960–1215 MHz | V_{CC} = 28 V | --- | 9.0 | --- | dB |

** Pulse width 10 μSec, duty cycle 1%.

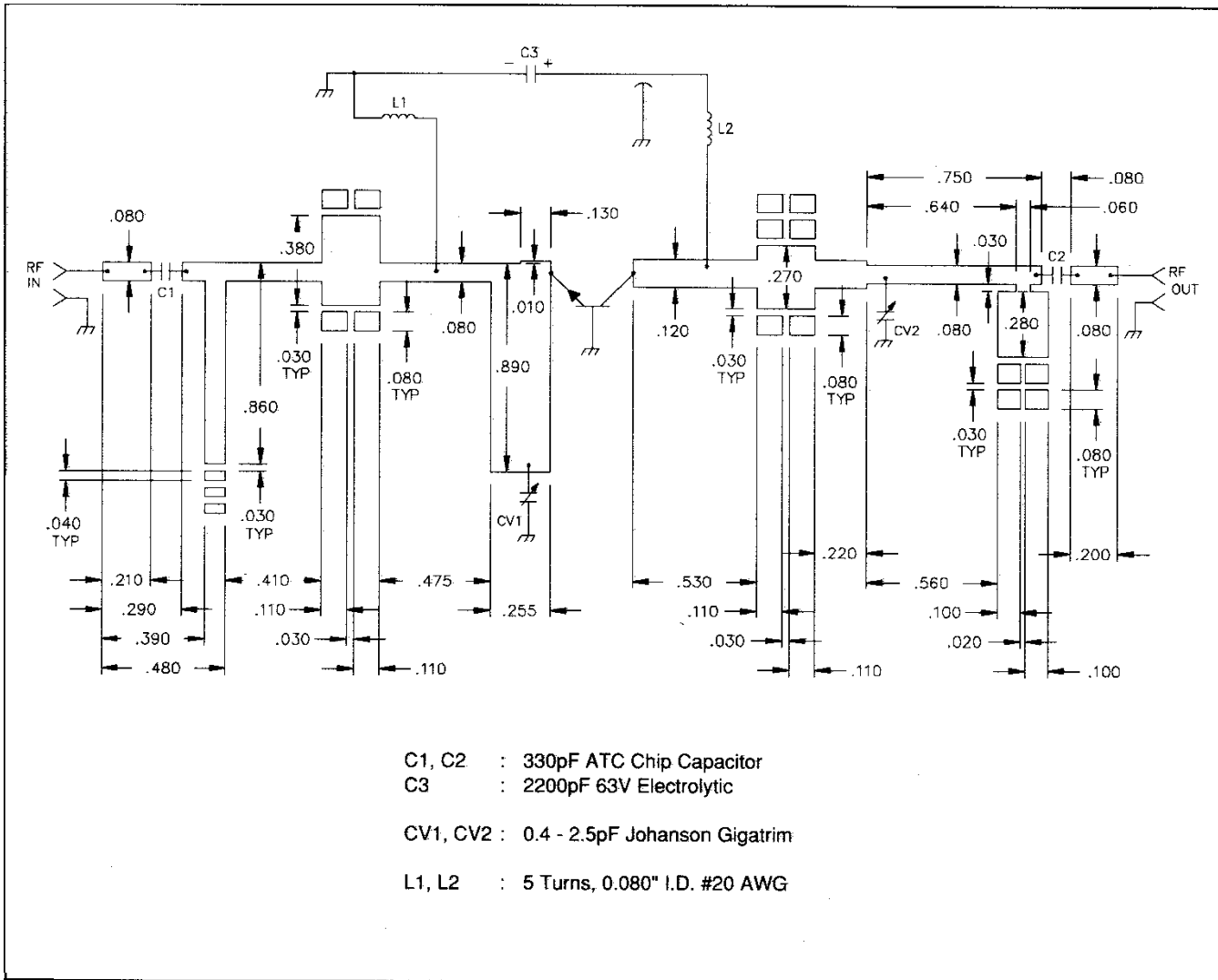
*** Pulse width 10 μSec, duty cycle 10%.

IMPEDANCE DATA

| Frequency | Z _{IN} (Ω) | Z _{CL} (Ω) |
|-----------|---------------------|---------------------|
| 1025 MHz | 11.0+ j 11.6 | 15 + j 22.0 |
| 1090 MHz | 12.5+ j 12.0 | 19 + j 19.5 |
| 1150 MHz | 12.2+ j 8.2 | 16 + j 20.5 |

SD1526-01

TEST CIRCUIT

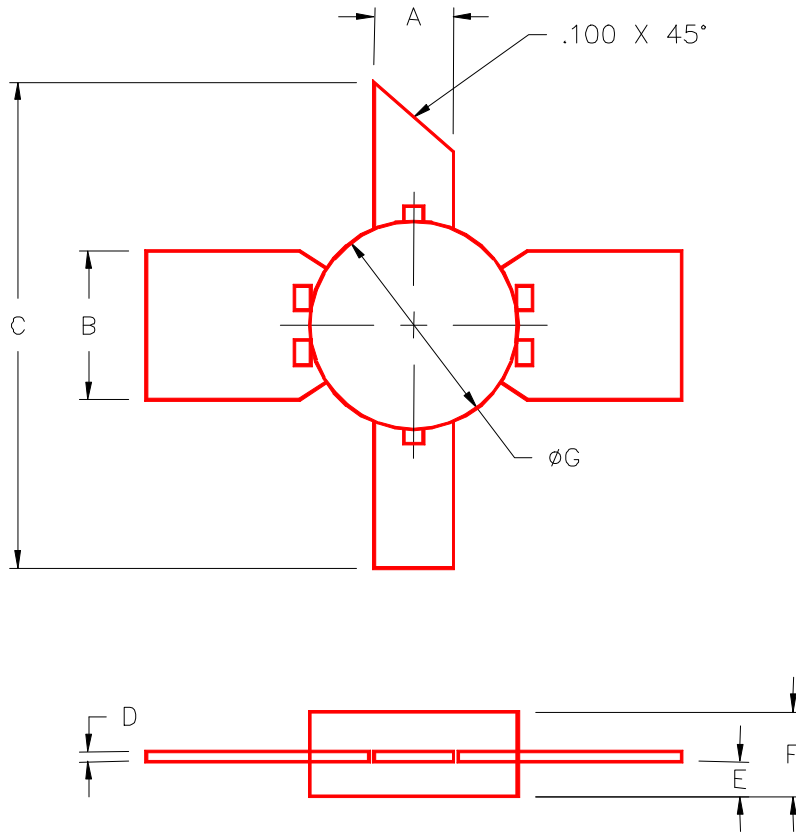


- C1, C2 : 330pF ATC Chip Capacitor
 C3 : 2200pF 63V Electrolytic
 CV1, CV2 : 0.4 - 2.5pF Johanson Gigatrim
 L1, L2 : 5 Turns, 0.080" I.D. #20 AWG

SD1526-01

PACKAGE MECHANICAL DATA

PACKAGE STYLE M115



| | MINIMUM INCHES/MM | MAXIMUM INCHES/MM | | MINIMUM INCHES/MM | MAXIMUM INCHES/MM |
|---|----------------------|----------------------|--|----------------------|----------------------|
| A | .095/2,41 | .105/2,67 | | | |
| B | .195/4,95 | .205/5,21 | | | |
| C | 1.000/25,40 | | | | |
| D | .004/0,10 | .007/0,18 | | | |
| E | .050/1,27 | .065/1,65 | | | |
| F | .120/3,05 | .135/3,43 | | | |
| G | .275/6,99 | .285/7,21 | | | |
| | | | | | |